MOSFET

Metal Oxide Semiconductor Field Effect Transistor

CoolMOS™ CFD2 650V

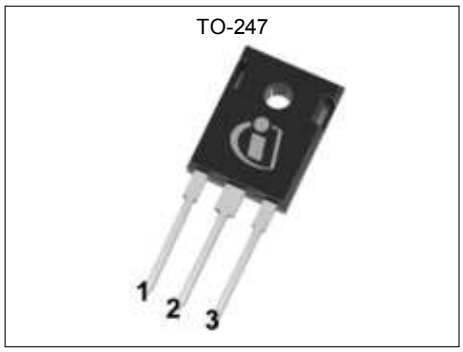
650V CoolMOS™ CFD2 Power Transistor
IPW65R041CFD

Data Sheet

Rev. 2.0
Final

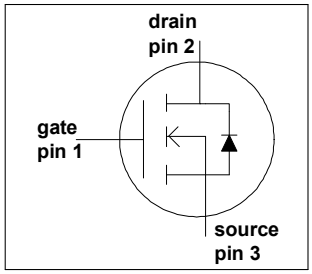
Industrial & Multimarket

1 Description



CoolMOS™ is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies. 650V CoolMOS™ CFD2 series combines the experience of the leading SJ MOSFET supplier with high class innovation. The resulting devices provide all benefits of a fast switching SJ MOSFET while offering an extremely fast and robust body diode. This combination of extremely low switching, commutation and conduction losses together with highest robustness make especially resonant switching applications more reliable, more efficient, lighter and cooler.

Features



- Ultra-fast body diode
- Very high commutation ruggedness
- Extremely low losses due to very low FOM Rdson*Qg and Eoss
- Easy to use/drive
- Pb-free plating, Halogen free mold compound
- Qualified for industrial grade applications according to JEDEC (J-STD20 and JESD22)

Applications

650V CoolMOS™ CFD2 is especially suitable for resonant switching PWM stages for e.g. PC Silverbox, LCD TV, Lighting, Server,Telecom and Solar.

Please note: For MOSFET paralleling the use of ferrite beads on the gate or separate totem poles is generally recommended.

Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS} @ $T_{j\ max}$	700	V
RDS(on),max	0.041	Ω
Qg,typ	300	nC
ID,pulse	255	A
Eoss @ 400V	22.5	µJ
Body diode di/dt	900	A/µs
Qrr	1.9	µC
trr	250	ns
Irrm	15	A

Type / Ordering Code	Package	Marking	Related Links
IPW65R041CFD	PG-TO 247	65F6041	see Appendix A

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2 Maximum ratings

at T_j = 25°C, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current[1]	I_D			68.5	A	T_C = 25°C
				43.3		T_C = 100°C
Pulsed drain current[2]	$I_{D,pulse}$			255	A	T_C = 25°C
Avalanche energy, single pulse	E_{AS}			2185	mJ	I_D = 13.7A, V_{DD} = 50V
Avalanche energy, repetitive	E_{AR}			3.31	mJ	I_D = 13.7A, V_{DD} = 50V
Avalanche current, repetitive	I_{AR}			13.7	A	
MOSFET dv/dt ruggedness	dv/dt			50	V/ns	V_{DS} = 0 ... 400V
Gate source voltage	V_{GS}	-20		20	V	static
		-30		30		AC (f > 1 Hz)
Power dissipation (non FullPAK) TO-247	P_{tot}			500.0	W	T_C = 25°C
Operating and storage temperature	T_j, T_{stg}	-55		150	°C	
Mounting torque (non FullPAK) TO-247				60	Ncm	M3 and M3.5 screws
Continuous diode forward current	I_S			68.5	A	T_C = 25°C
Diode pulse current	$I_{S,pulse}$			255	A	T_C = 25°C
Reverse diode dv/dt[3]	dv/dt			50	V/ns	V_{DS} = 0 ... 400V, $I_{SD} \le I_D$, T_j = 25°C
Maximum diode commutation speed	di_f/dt			900	A/µs	

[1] Limited by $T_{j\,max}$.
[2] Pulse width t_p limited by $T_{j\,max}$
[3] $V_{peak}<V_{(BR)DSS}$, $T_j<T_{j\,max}$, identical low and high side switch with same Rg

3 Thermal characteristics

Table 3 Thermal characteristics TO-247

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}			0.25	°C/W	
Thermal resistance, junction - ambient	R_{thJA}			62	°C/W	leaded
Soldering temperature, wavesoldering only allowed at leads	T_{sold}			260	°C	1.6 mm (0.063 in.) from case for 10s

4 Electrical characteristics

at T_j = 25°C, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	650			V	V_{GS} = 0V, I_D = 1mA
Gate threshold voltage	$V_{GS(th)}$	3.5	4	4.5	V	V_{DS} = V_{GS}, I_D = 3.3mA
Zero gate voltage drain current	I_{DSS}			3.5	µA	V_{DS} = 650V, V_{GS} = 0V, T_j = 25°C
			1000			V_{DS} = 650V, V_{GS} = 0V, T_j = 150°C
Gate-source leakage current	I_{GSS}			100	nA	V_{GS} = 20V, V_{DS} = 0V
Drain-source on-state resistance	$R_{DS(on)}$		0.037	0.041	Ω	V_{GS} = 10V, I_D = 33.1A, T_j = 25°C
			0.096			V_{GS} = 10V, I_D = 33.1A, T_j = 150°C
Gate resistance	R_G		0.7		Ω	f = 1MHz, open drain

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}		8400		pF	V_{GS} = 0V, V_{DS} = 100V, f = 1MHz
Output capacitance	C_{oss}		400		pF	
Effective output capacitance, energy related[1)]	$C_{o(er)}$		288		pF	V_{GS} = 0V, V_{DS} = 0 ... 400V
Effective output capacitance, time related[2)]	$C_{o(tr)}$		1485		pF	I_D = constant, V_{GS} = 0V, V_{DS} = 0 ... 400V
Turn-on delay time	$t_{d(on)}$		34		ns	V_{DD} = 400V, V_{GS} = 13V, I_D = 49.6A, R_G = 1.8Ω
Rise time	t_r		28		ns	
Turn-off delay time	$t_{d(off)}$		127		ns	
Fall time	t_f		8		ns	

Table 6 Gate charge characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}		54		nC	V_{DD} = 480V, I_D = 49.6A, V_{GS} = 0 to 10V
Gate to drain charge	Q_{gd}		165		nC	
Gate charge total	Q_g		300		nC	
Gate plateau voltage	$V_{plateau}$		6.5		V	

[1)] $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 400V

[2)] $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 400V

Table 7 Reverse diode characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	V_{SD}		1		V	V_{GS} = 0V, I_F = 49.6A, T_j = 25°C
Reverse recovery time	t_{rr}		250		ns	V_R = 400V, I_F = 49.6A, dI_F/dt = 100A/µs
Reverse recovery charge	Q_{rr}		1.9		µC	
Peak reverse recovery current	I_{rrm}		15		A	

5 Electrical characteristics diagrams

Table 8

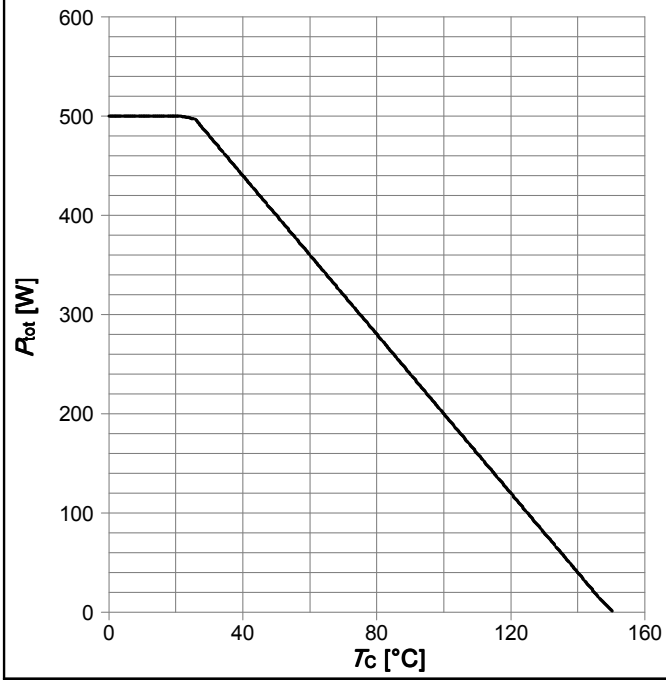
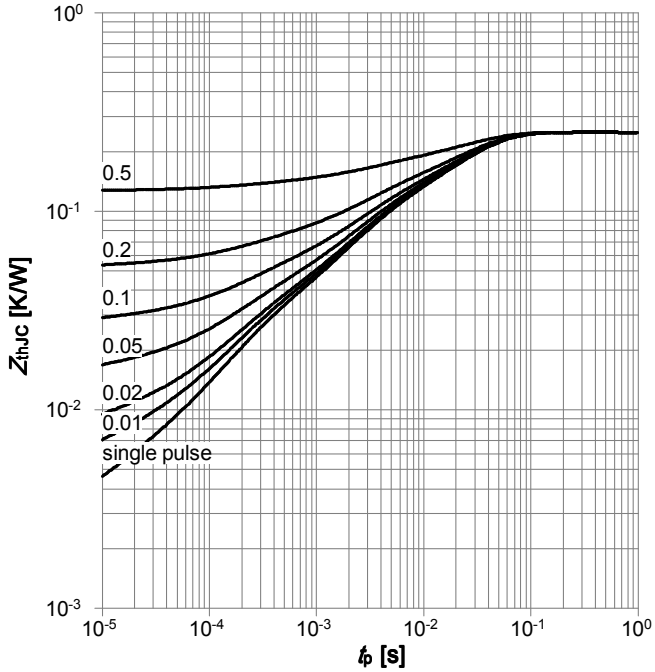
Power dissipation (Non FullPAK)	Max. transient thermal impedance (Non FullPAK)
	
$P_{tot}=f(T_C)$	$Z_{thJC}=f(t_P)$; parameter: $D=t_p/T$

Table 9

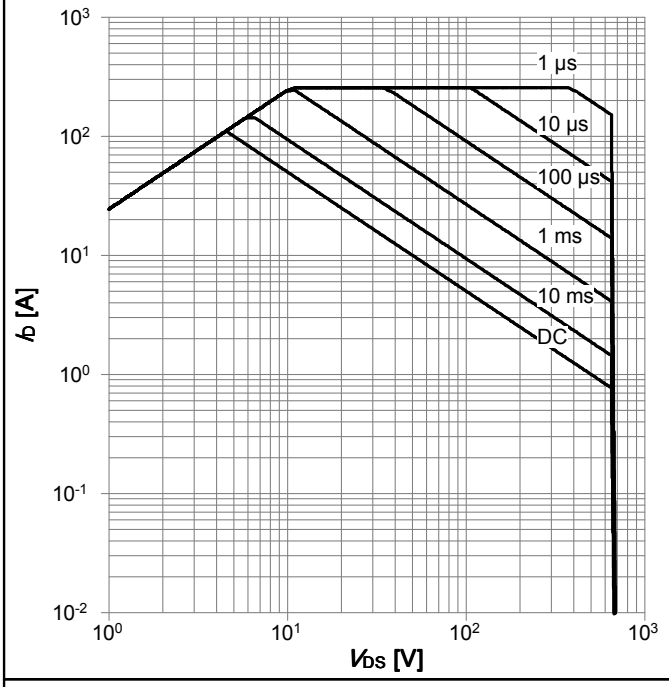
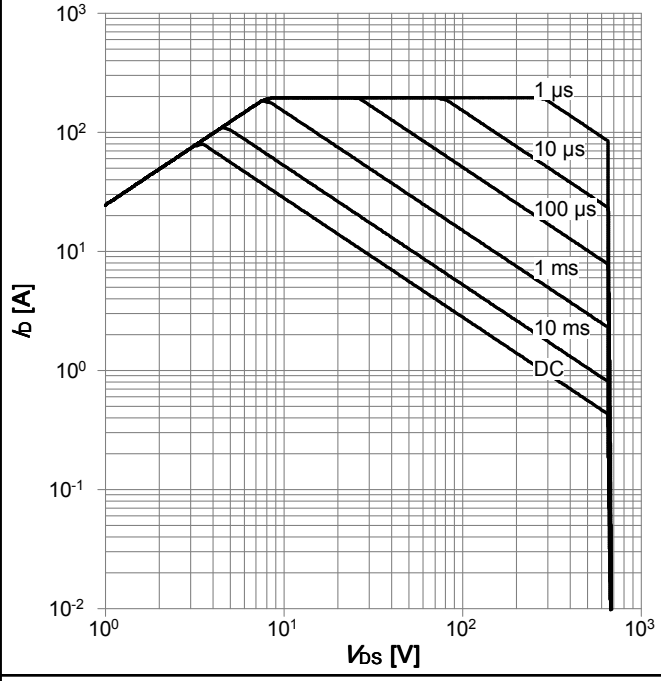
Safe operating area T_C=25°C (Non FullPAK)	Safe operating area T_C=80°C (Non FullPAK)
	
$I_D=f(V_{DS})$; T_C=25 °C; D=0; parameter: t_p;Vgs>7.5V;	$I_D=f(V_{DS})$; T_C=80 °C; D=0; parameter: t_p; Vgs>7.5V;

Table 10

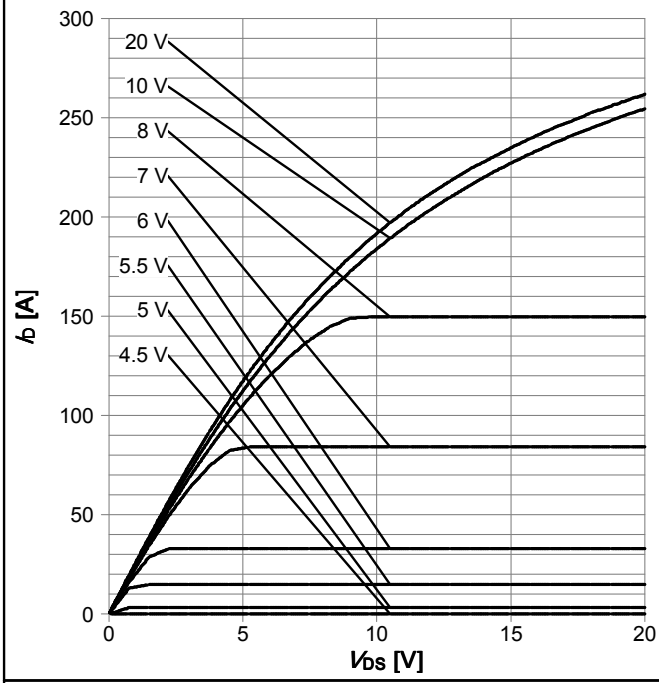
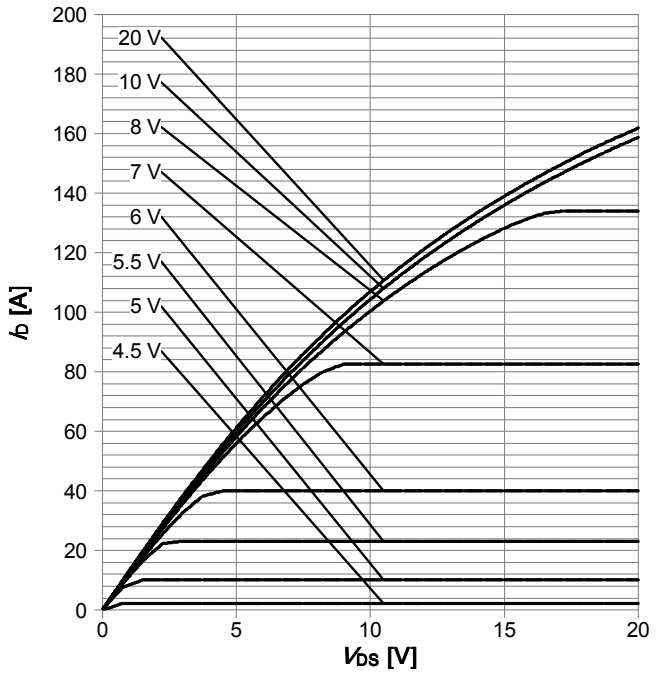
Typ. output characteristics T_C=25°C	Typ. output characteristics T_C=125°C
	
I_D=f(V_{DS}); T_j=25 °C; parameter: V_{GS}	I_D=f(V_{DS}); T_j=125 °C; parameter: V_{GS}

Table 11

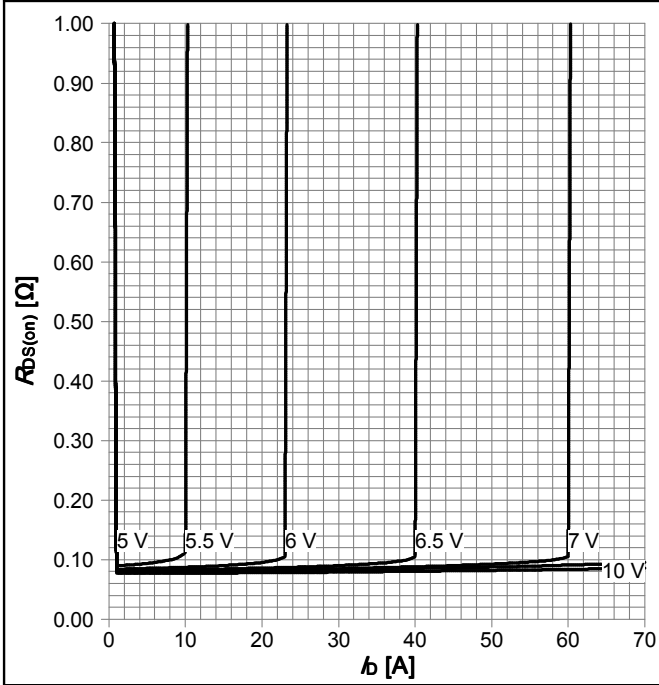
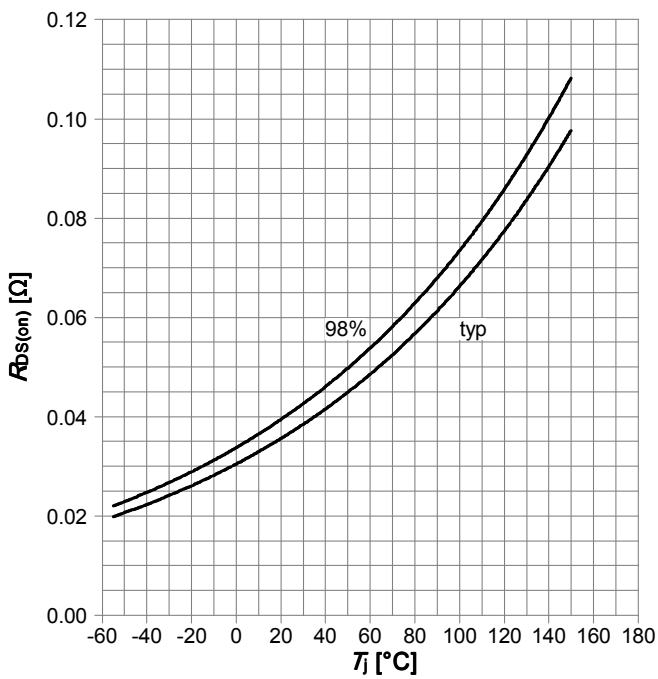
Typ. drain-source on-state resistance	Drain-source on-state resistance
	
$R_{DS(on)}$=f(I_D); T_j=125 °C; parameter: V_{GS}	$R_{DS(on)}$=f(T_j); I_D=33.1 A; V_{GS}=10 V

Table 12

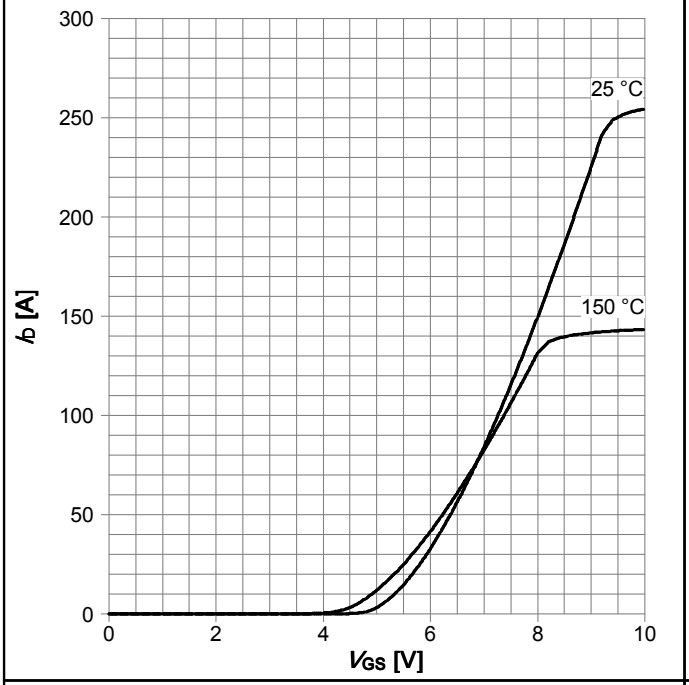
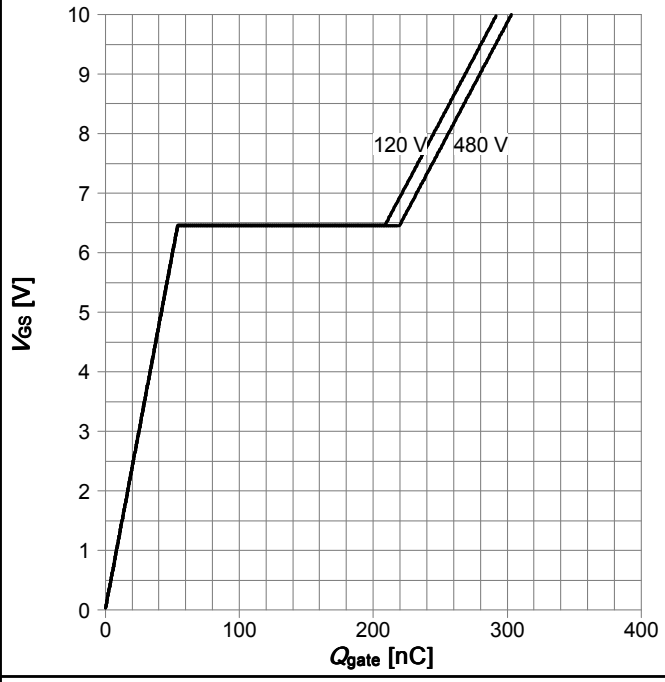
Typ. transfer characteristics	Typ. gate charge
	
$I_D=f(V_{GS})$; $\lvert V_{DS}\rvert$=20V;	$V_{GS}=f(Q_{gate})$; I_D=49.6 A pulsed; parameter: V_{DD}

Table 13

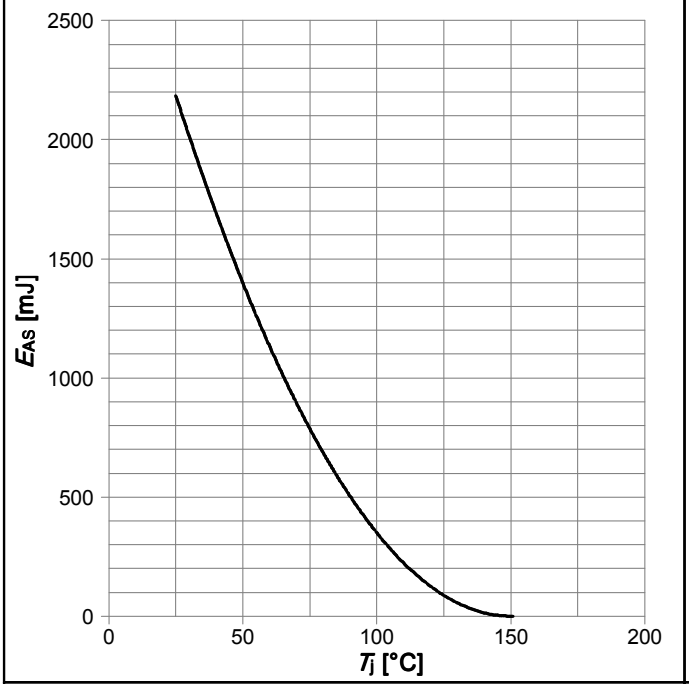
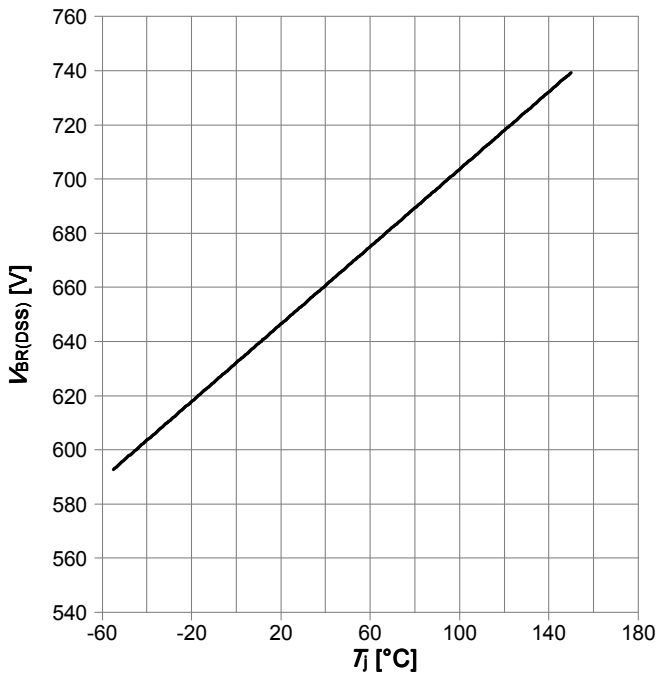
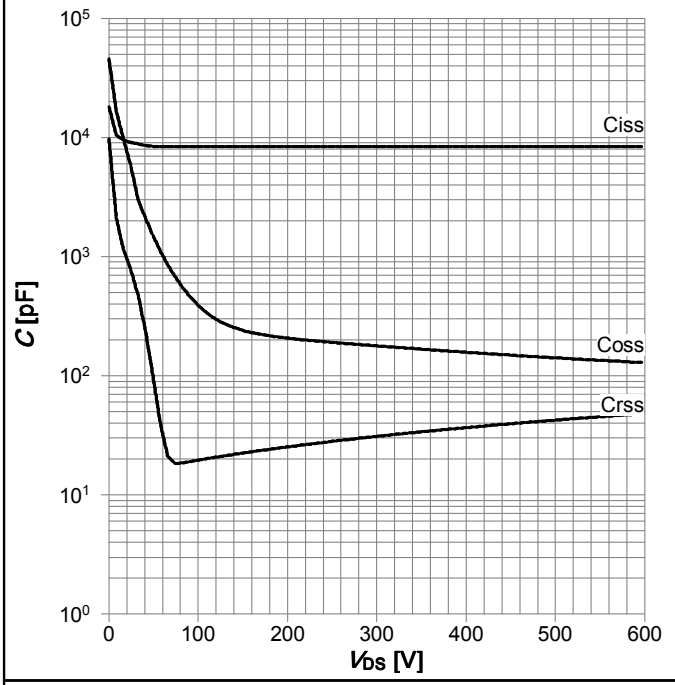
Avalanche energy	Drain-source breakdown voltage
	
$E_{AS}=f(T_j)$; I_D=13.7A; V_{DD}=50 V	$V_{BR(DSS)}=f(T_j)$; I_D=10 mA

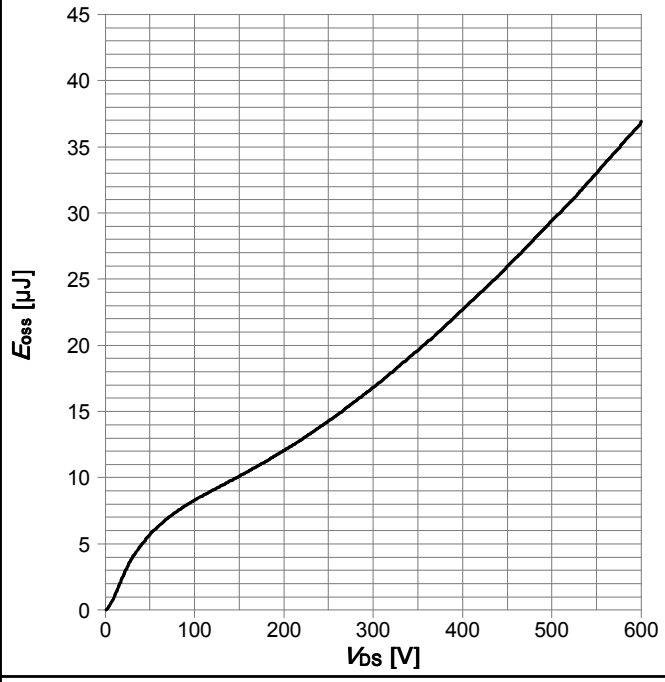
Table 14

Typ. capacitances



C=f(V_{DS}); V_{GS}=0 V; f=1 MHz

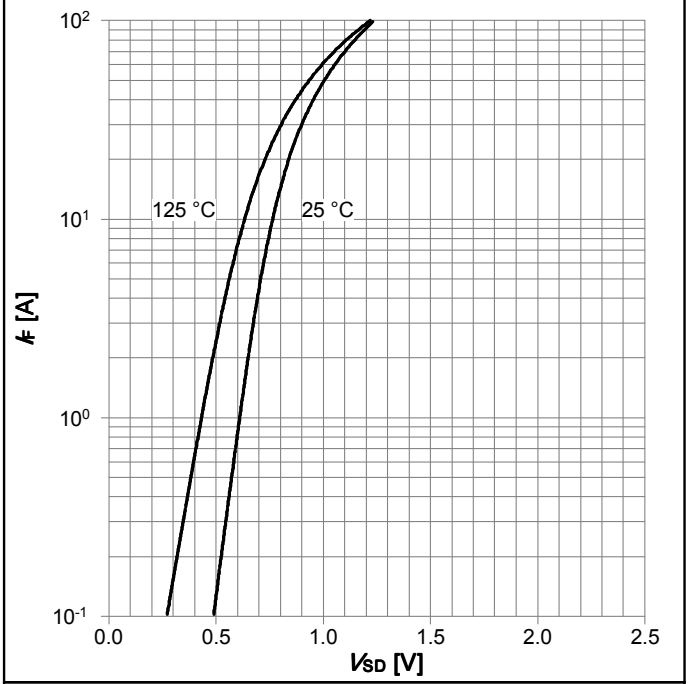
Typ. C_{oss} stored energy



E_{oss}=f(V_{DS})

Table 15

Forward characteristics of reverse diode



I_F=f(V_{SD}); parameter: T_j

6 Test Circuits

Table 16 Diode_characteristics

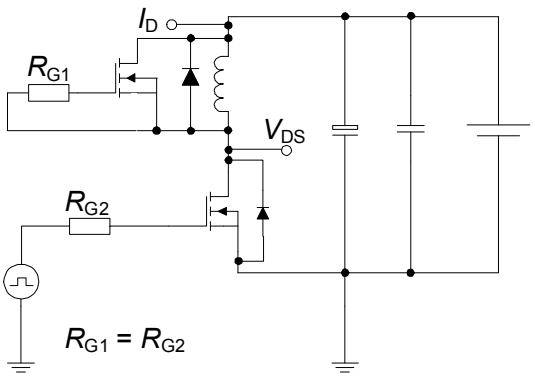
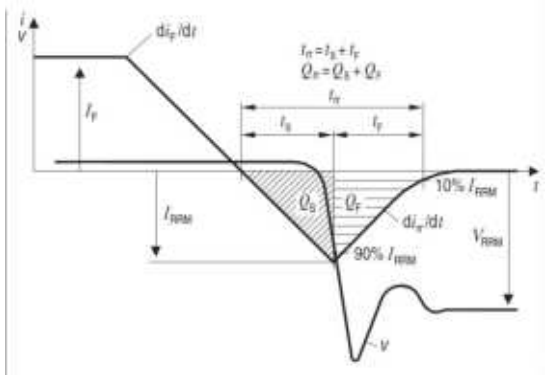
Test circuit for diode characteristics	Diode recovery waveform
	

Table 17 Switching_times

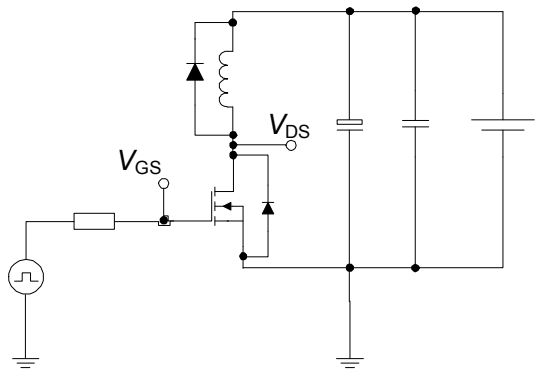
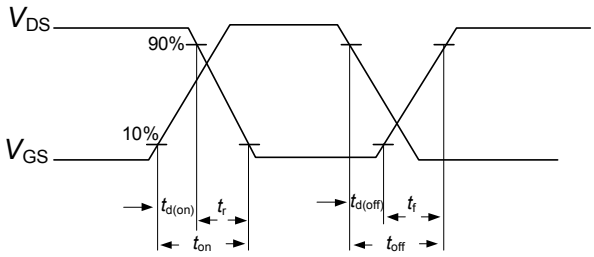
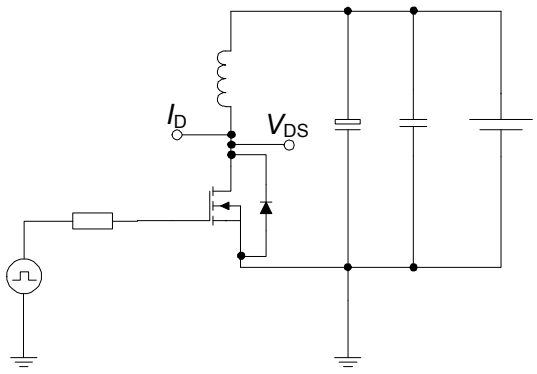
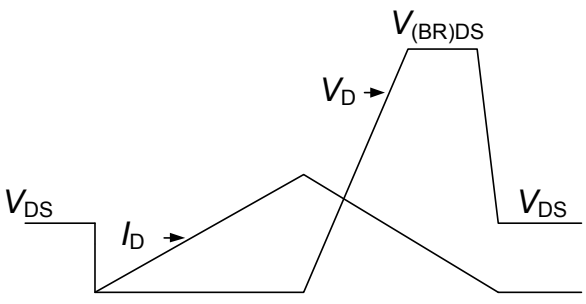
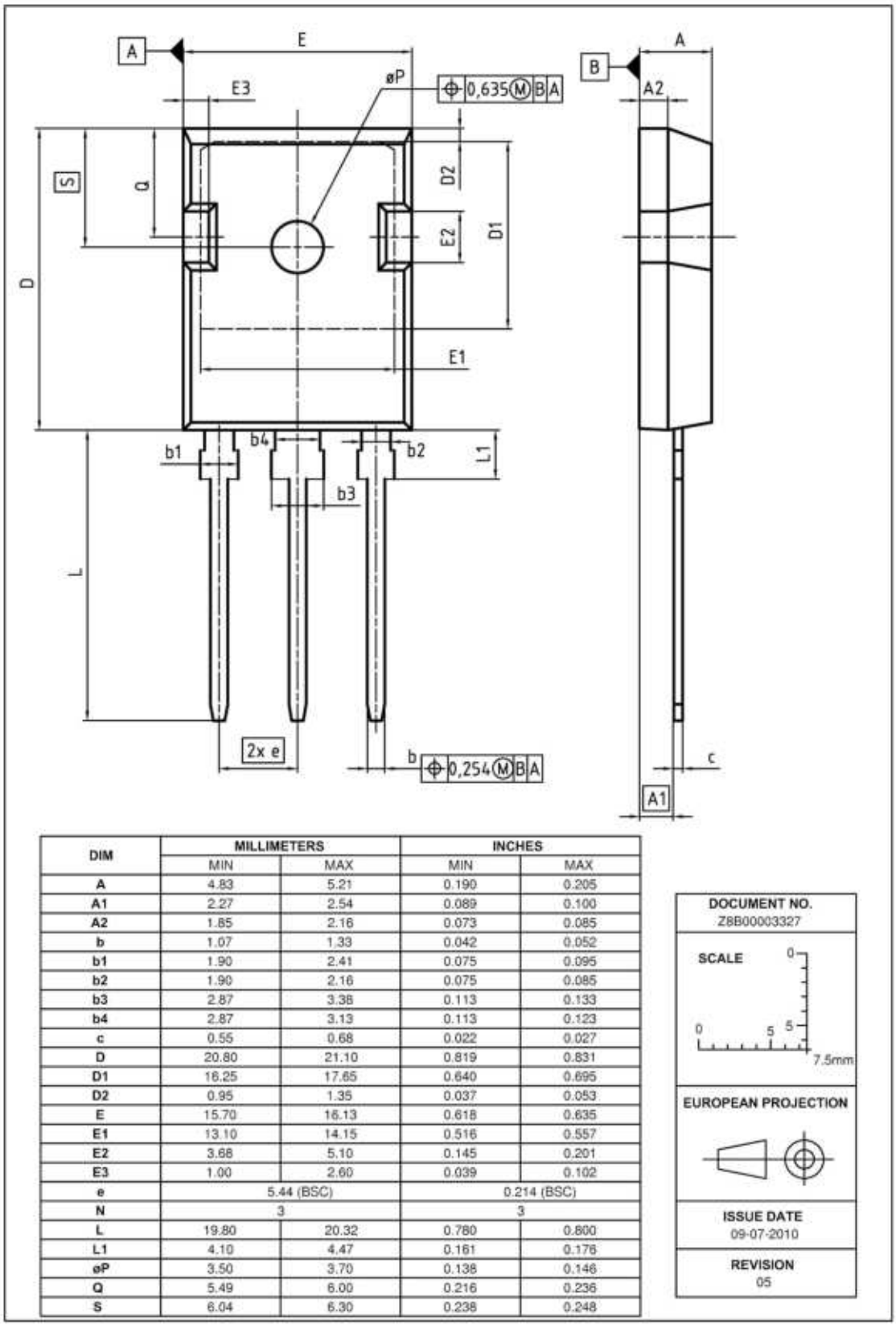
Switching times test circuit for inductive load	Switching times waveform
	

Table 18 Unclamped_inductive

Unclamped inductive load test circuit	Unclamped inductive waveform
	

7 Package Outlines



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.83	5.21	0.190	0.205
A1	2.27	2.54	0.089	0.100
A2	1.85	2.16	0.073	0.085
b	1.07	1.33	0.042	0.052
b1	1.90	2.41	0.075	0.095
b2	1.90	2.16	0.075	0.085
b3	2.87	3.38	0.113	0.133
b4	2.87	3.13	0.113	0.123
c	0.55	0.68	0.022	0.027
D	20.80	21.10	0.819	0.831
D1	16.25	17.65	0.640	0.695
D2	0.95	1.35	0.037	0.053
E	15.70	16.13	0.618	0.635
E1	13.10	14.15	0.516	0.557
E2	3.68	5.10	0.145	0.201
E3	1.00	2.60	0.039	0.102
e	5.44 (BSC)		0.214 (BSC)	
N	3		3	
L	19.80	20.32	0.780	0.800
L1	4.10	4.47	0.161	0.176
øP	3.50	3.70	0.138	0.146
Q	5.49	6.00	0.216	0.236
S	6.04	6.30	0.238	0.248

DOCUMENT NO.
Z8B00003327

SCALE 0 5 5 7.5mm

EUROPEAN PROJECTION

ISSUE DATE
09-07-2010

REVISION
05

Figure 1 Outline PG-TO 247, dimensions in mm/inches

8 Appendix A

Table 19 Related Links

- **IFX Design Tools:**
  http://www.infineon.com/cms/en/product/promopages/designtools/index.html
- **IFX CoolMOS Webpage:**
  http://www.infineon.com/cms/en/product/channel.html?channel=ff80808112ab681d0112ab6a628704d8

Revision History

IPW65R041CFD

Revision: 2011-10-13, Rev. 2.0

Previous Revision		
Revision	Date	Subjects (major changes since last revision)
2.0	2011-10-13	release of final datasheet

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